ESD Protection Diodes

In Ultra Small SOT-723 Package

The μESD Series is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time, make these parts ideal for ESD protection on designs where board space is at a premium. Because of its small size, it is suited for use in cellular phones, portable devices, digital cameras, power supplies and many other portable applications.

Specification Features:

• Small Body Outline Dimensions: 0.047" x 0.032" (1.20 mm x 0.80 mm)

Low Body Height: 0.020" (0.5 mm)
Stand-off Voltage: 3.3 V - 6.0 V

• Low Leakage

• Response Time is Typically < 1 ns

• ESD Rating of Class 3 (> 16 kV) per Human Body Model

• IEC61000-4-2 Level 4 ESD Protection

• IEC61000-4-4 Level 4 EFT Protection

• AEC-Q101 Qualified and PPAP Capable

• These are Pb-Free Devices

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic

Epoxy Meets UL 94 V-0

LEAD FINISH: 100% Matte Sn (Tin)

MOUNTING POSITION: Any

QUALIFIED MAX REFLOW TEMPERATURE: 260°C

Device Meets MSL 1 Requirements

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|-----------------------------------|-------------------|---------------------|
| IEC 61000-4-2 (ESD) Air Contact | | ±30 ±30 | kV |
| IEC 61000-4-4 (EFT) | | 40 | Α |
| ESD Voltage Per Human Body Model Per Machine Model | | 16 400 | kV V |
| Total Power Dissipation on FR-5 Board (Note 1) @ T _A = 25°C Derate above 25°C Thermal Resistance Junction-to-Ambient | P_D | 240 1.9 525 | mW mW/°C °C/W |
| Junction and Storage Temperature Range | T _J , T _{stg} | –55 to +150 | °C |
| Lead Solder Temperature – Maximum (10 Second Duration) | T _L | 260 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

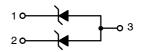
1. $FR-5 = 1.0 \times 0.75 \times 0.62$ in.



ON Semiconductor®

http://onsemi.com

PIN 1. CATHODE 2. CATHODE 3. ANODE





SOT-723 CASE 631AA STYLE 4





xx = Device Code M = Date Code

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|------------|---------|-----------------------|
| UESDxxDT5G | SOT-723 | 8000/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

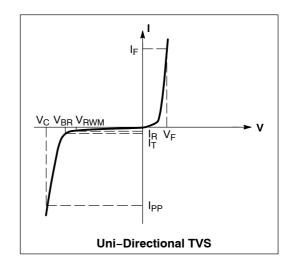
DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the table on page 2 of this data sheet.

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

| Symbol | Parameter |
|-----------------|--|
| I _{PP} | Maximum Reverse Peak Pulse Current |
| V _C | Clamping Voltage @ IPP |
| V_{RWM} | Working Peak Reverse Voltage |
| I _R | Maximum Reverse Leakage Current @ V _{RWM} |
| V_{BR} | Breakdown Voltage @ I _T |
| Ι _Τ | Test Current |
| I _F | Forward Current |
| V _F | Forward Voltage @ I _F |
| P_{pk} | Peak Power Dissipation |
| С | Max. Capacitance @V _R = 0 and f = 1 MHz |

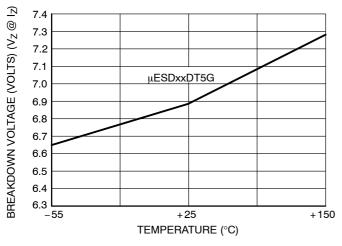


ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted, $V_F = 1.1 \text{ V Max.}$ @ $I_F = 10 \text{ mA}$ for all types)

| | Device | V _{RWM} (V) | I _R (μΑ) @ V _{RWM} | V _{BR} (V) @ I _T (Note 2) | I _T | C (pF) |
|-------------|---------|----------------------|--|--|----------------|--------|
| Device* | Marking | Max | Max | Min | mA | Тур |
| UESD3.3DT5G | L0 | 3.3 | 1.0 | 5.0 | 1.0 | 47 |
| UESD5.0DT5G | L2 | 5.0 | 0.1 | 6.2 | 1.0 | 38 |
| UESD6.0DT5G | L3 | 6.0 | 0.1 | 7.0 | 1.0 | 34 |

^{*}Other voltages available upon request. 2. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.

TYPICAL CHARACTERISTICS

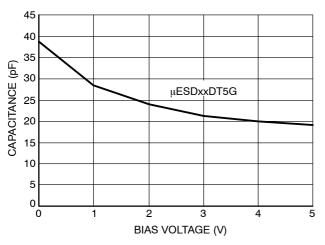


20
18
16
14
12
10
18
6
4
2
0
-55
+25
+150

TEMPERATURE (°C)

Figure 1. Typical Breakdown Voltage versus Temperature

Figure 2. Typical Leakage Current versus Temperature



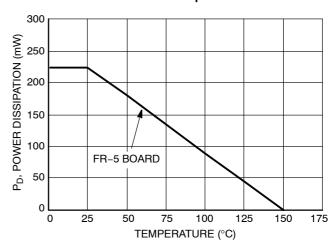
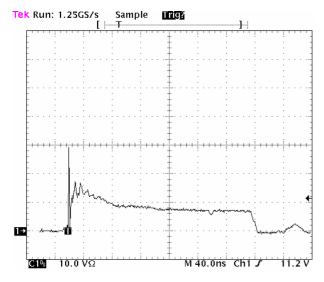


Figure 3. Typical Capacitance versus Bias Voltage

Figure 4. Steady State Power Derating Curve



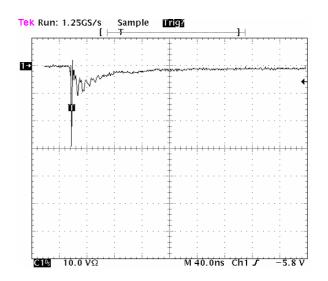
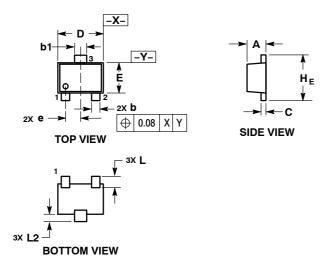


Figure 5. Positive 8 kV contact per IEC 6100-4-2 - μESD5.0DT5G

Figure 6. Negative 8 kV contact per IEC 61000-4-2 - μESD5.0DT5G

PACKAGE DIMENSIONS

SOT-723 CASE 631AA ISSUE D



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14 5M 1994
- CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS

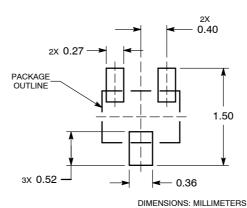
| | MILLIMETERS | | | |
|-----|-------------|------|------|--|
| DIM | MIN | NOM | MAX | |
| Α | 0.45 | 0.50 | 0.55 | |
| b | 0.15 | 0.21 | 0.27 | |
| b1 | 0.25 | 0.31 | 0.37 | |
| С | 0.07 | 0.12 | 0.17 | |
| D | 1.15 | 1.20 | 1.25 | |
| Е | 0.75 | 0.80 | 0.85 | |
| е | 0.40 BSC | | | |
| ΗE | 1.15 | 1.20 | 1.25 | |
| L | 0.29 REF | | | |
| 12 | 0.15 | 0.20 | 0.25 | |

STYLE 4:

PIN 1. CATHODE

2. CATHODE 3. ANODE

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering

details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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